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## Correction: Effect of yttrium feeding time on the electrical and structural properties of atomic layer deposited Y-doped TiO<sub>2</sub> films for dynamic random-access memory capacitors

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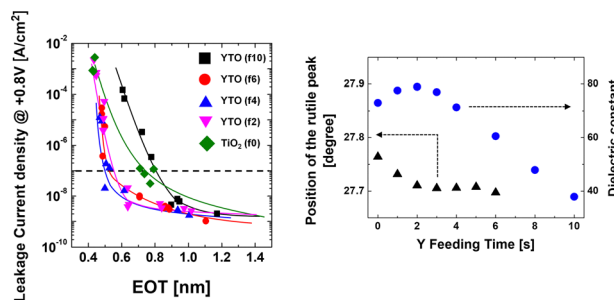
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Correction for 'Effect of yttrium feeding time on the electrical and structural properties of atomic layer deposited Y-doped TiO<sub>2</sub> films for dynamic random-access memory capacitors' by Tae Kyun Kim *et al.*, *J. Mater. Chem. C*, 2025, **13**, 16969–16980, <https://doi.org/10.1039/D5TC01401H>.

The authors regret errors in the graphical abstract, Fig. 5c and 7a in the published article, which resulted from an error during selection of representative plots among datasets measured under different Y-feeding-time conditions. The captions and manuscript text remain unchanged; these changes do not affect the conclusions. The corrected images for the graphical abstract, Fig. 5 and 7 are as shown here. The graphical abstract for the original published article has been updated accordingly.

Graphical abstract:



The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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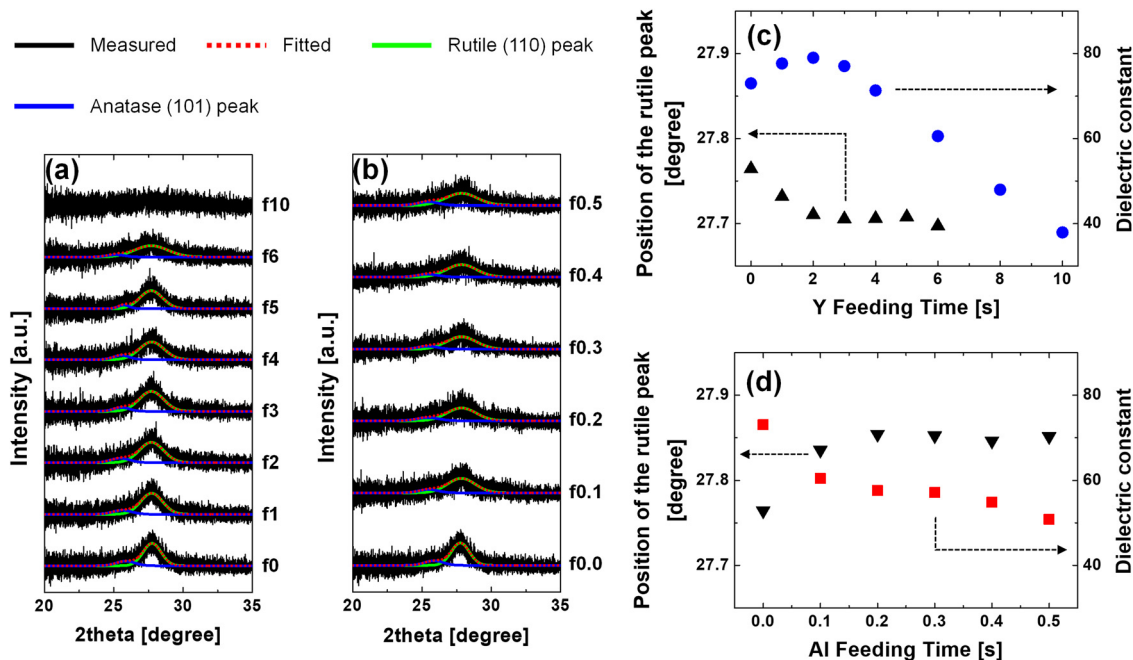


Fig. 5 GIXRD patterns of (a) Y- and (b) Al-doped TiO<sub>2</sub> films (~20 nm thick) with varying dopant feeding times. Peak position of the rutile (110) phase and the dielectric constant of the ~20 nm-thick (c) Y- and (d) Al-doped TiO<sub>2</sub> films as a function of the dopant feeding time.

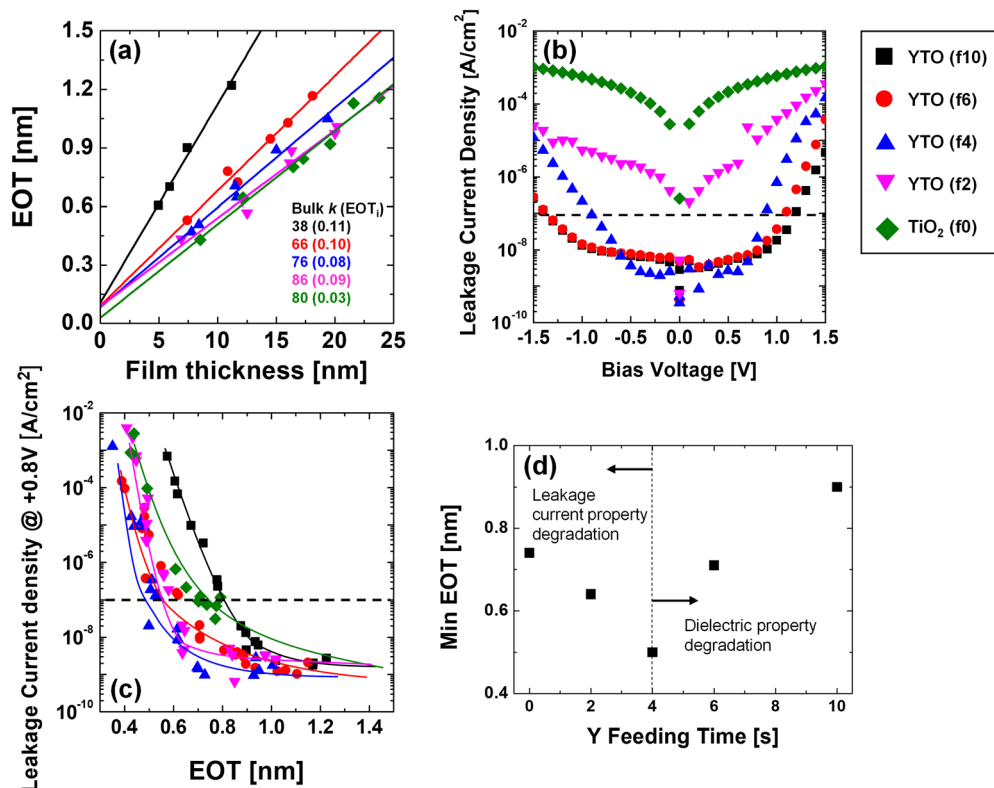


Fig. 7 (a) EOT-POT plot and (b) J-V plot of ~8 nm-thick films and (c) J-EOT graph and (d) minimum EOT plot of TiO<sub>2</sub> and YTO films with varying Y feeding times.

